



Description

The XPX30120RD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

$V_{DS} = 30V, I_D = 120A$

$R_{DS(ON)} = 1.9m\Omega$ (typ) @ $V_{GS} = 10V$

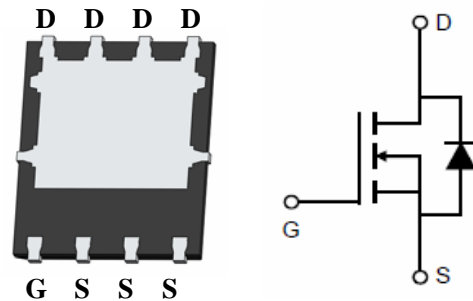
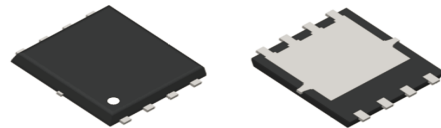
$R_{DS(ON)} = 2.2m\Omega$ (typ) @ $V_{GS} = 4.5V$

General Features

- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|----------|
| XPX30120RD | XPX30120RD | DFN5X6-8L | - | - | - |

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|--------------------|------------|---------------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 120 | A |
| Drain Current-Continuous ($T_C = 100^\circ C$) | $I_D(100^\circ C)$ | 85 | A |
| Pulsed Drain Current | I_{DM} | 420 | A |
| Maximum Power Dissipation | P_D | 75 | W |
| Derating factor | | 0.65 | W/ $^\circ C$ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | $^\circ C$ |
| Thermal Resistance, Junction-to-Case ^(Note 2) | $R_{\theta JC}$ | 1.87 | $^\circ C/W$ |

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|--------------|--|-----|------|-----------|------------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 30 | 35 | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=30V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | - | - | ± 100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 0.7 | 1.1 | 1.7 | V |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=20A$ | - | 1.9 | 2.2 | m Ω |
| | | $V_{GS}=4.5V, I_D=15A$ | | 2.2 | 2.9 | |
| Forward Transconductance | g_{FS} | $V_{DS}=10V, I_D=20A$ | 35 | - | - | S |
| Dynamic Characteristics (Note 4) | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$ | - | 6869 | - | PF |
| Output Capacitance | C_{oss} | | - | 974 | - | PF |
| Reverse Transfer Capacitance | C_{rss} | | - | 740 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=15V, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$ | - | 25 | - | nS |
| Turn-on Rise Time | t_r | | - | 26 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 98 | - | nS |
| Turn-Off Fall Time | t_f | | - | 40 | - | nS |
| Total Gate Charge | Q_g | $V_{DS}=15V, I_D=20A,$ $V_{GS}=10V$ | - | 142 | | nC |
| Gate-Source Charge | Q_{gs} | | - | 21 | | nC |
| Gate-Drain Charge | Q_{gd} | | - | 33 | | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V_{SD} | $V_{GS}=0V, I_S=20A$ | - | | 1.2 | V |
| Diode Forward Current (Note 2) | I_S | | - | - | 110 | A |
| Reverse Recovery Time | t_{rr} | $T_J = 25^\circ\text{C}, I_F = 20A$ $di/dt = 100A/\mu s$ (Note 3) | - | 20 | - | nS |
| Reverse Recovery Charge | Q_{rr} | | - | 55 | - | nC |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics (Curves)

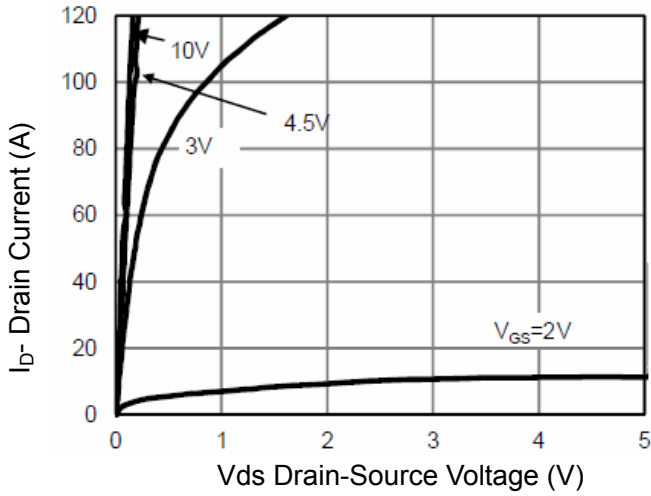


Figure 1 Output Characteristics

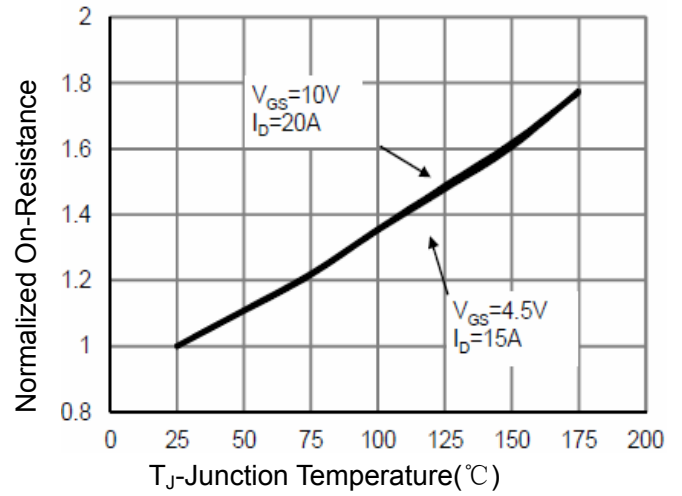


Figure 4 Rds(on)-Junction Temperature

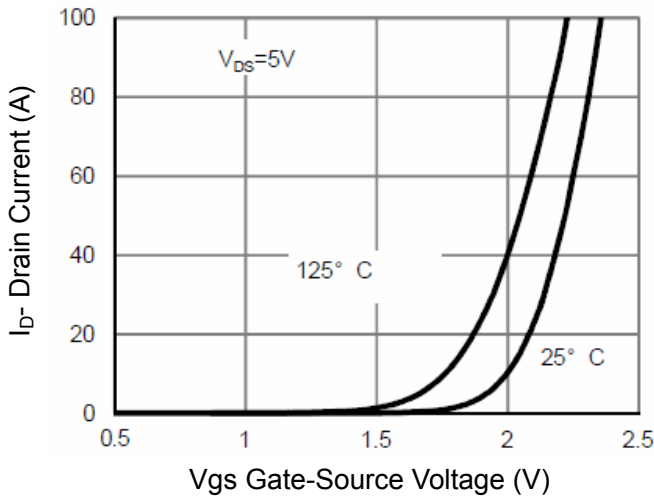


Figure 2 Transfer Characteristics

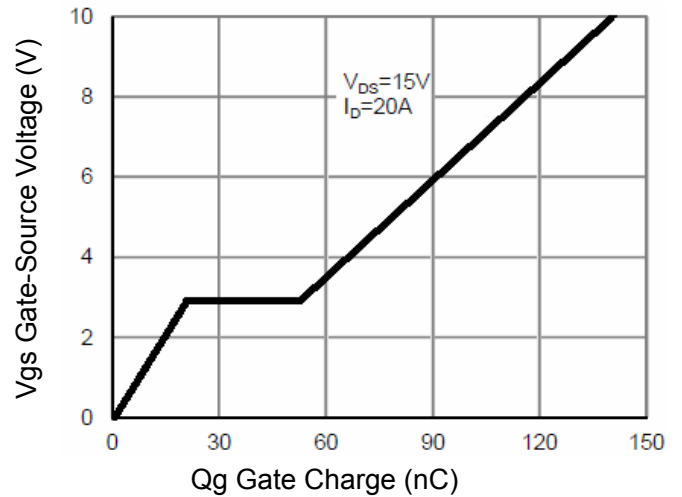


Figure 5 Gate Charge

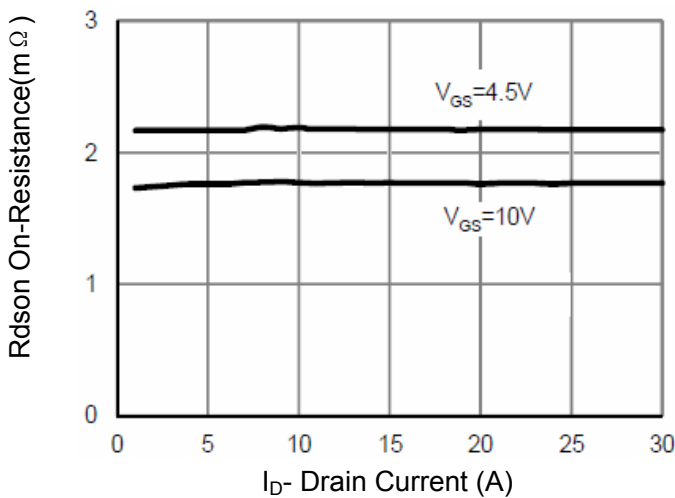


Figure 3 Rds(on)- Drain Current

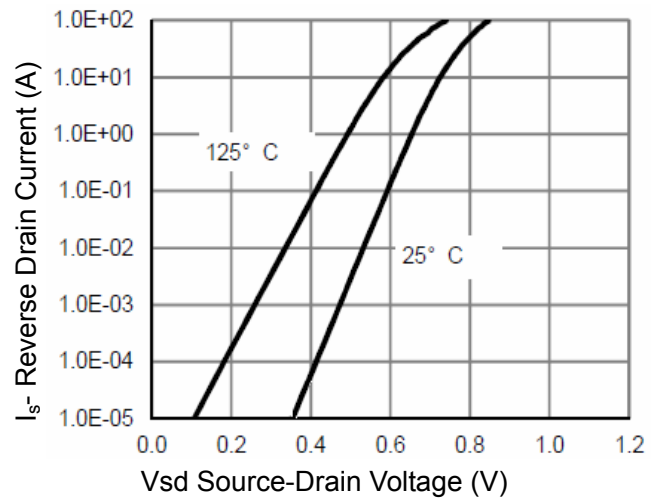


Figure 6 Source- Drain Diode Forward

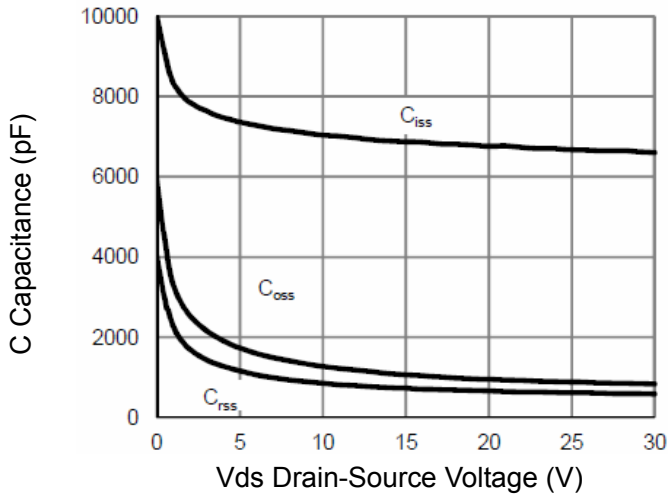


Figure 7 Capacitance vs Vds

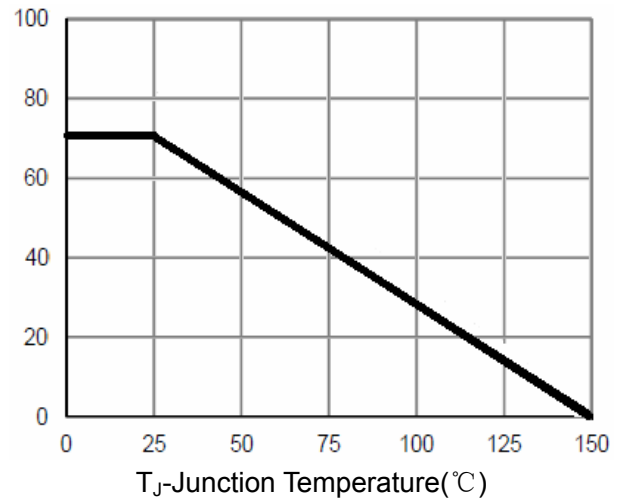


Figure 9 BV_{DSS} vs Junction Temperature

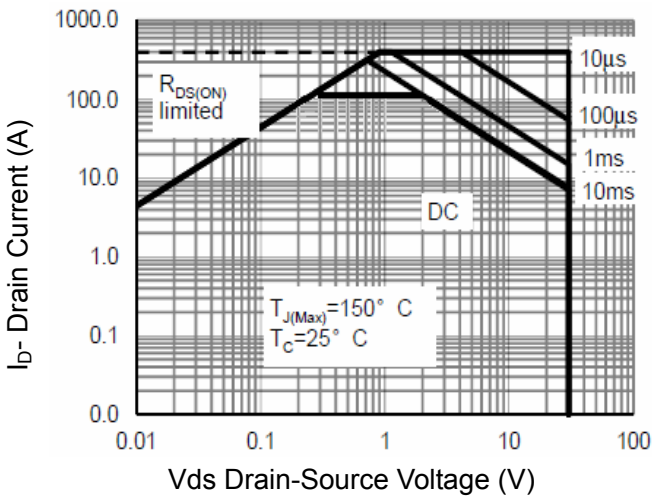


Figure 8 Safe Operation Area

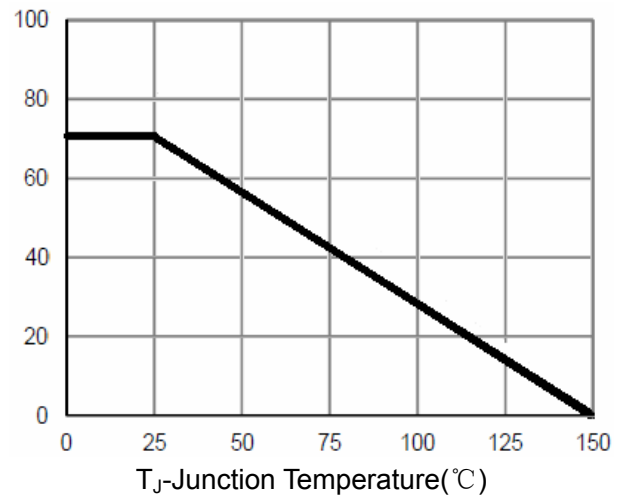


Figure 10 $V_{GS(th)}$ vs Junction Temperature

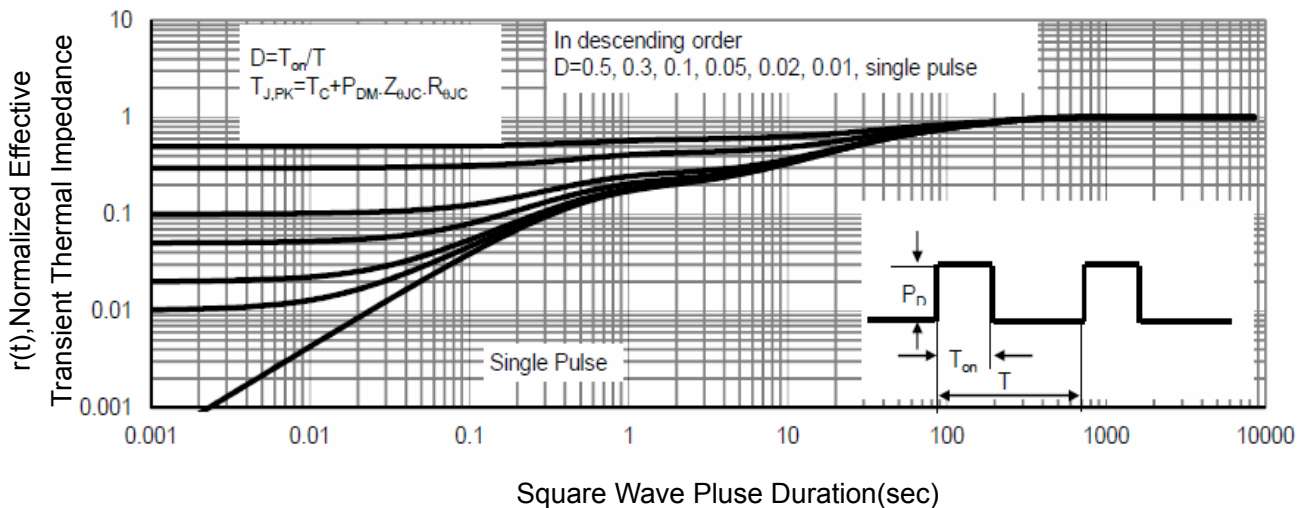
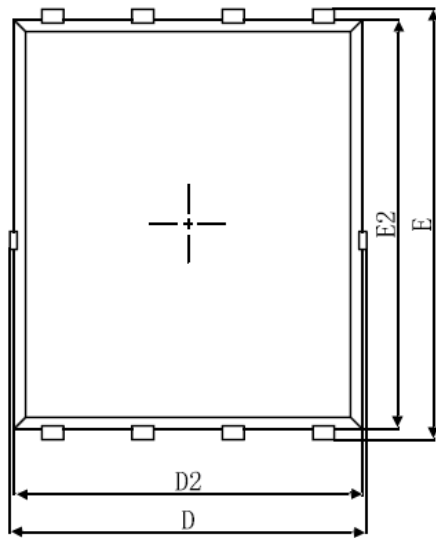
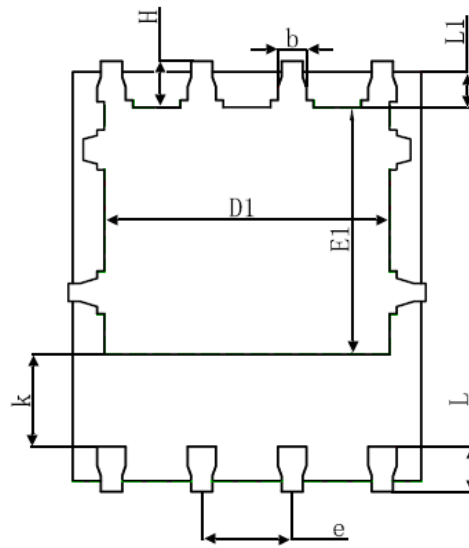


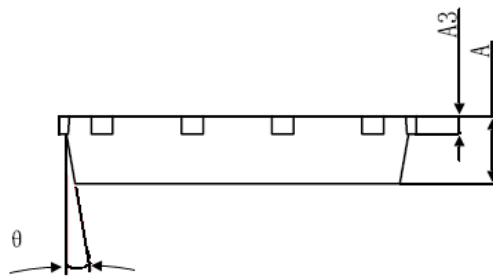
Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information


Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.000 | 0.035 | 0.039 |
| A3 | 0.254REF. | | 0.010REF. | |
| D | 4.944 | 5.096 | 0.195 | 0.201 |
| E | 5.974 | 6.126 | 0.235 | 0.241 |
| D1 | 3.910 | 4.110 | 0.154 | 0.162 |
| E1 | 3.375 | 3.575 | 0.133 | 0.141 |
| D2 | 4.824 | 4.976 | 0.190 | 0.196 |
| E2 | 5.674 | 5.826 | 0.223 | 0.229 |
| k | 1.190 | 1.390 | 0.047 | 0.055 |
| b | 0.350 | 0.450 | 0.014 | 0.018 |
| e | 1.270TYP. | | 0.050TYP. | |
| L | 0.559 | 0.711 | 0.022 | 0.028 |
| L1 | 0.424 | 0.576 | 0.017 | 0.023 |
| H | 0.574 | 0.726 | 0.023 | 0.029 |
| θ | 8° | 12° | 8° | 12° |

Flow (wave) soldering (solder dipping)

| Product | Peak Temperature | Dipping Time |
|----------------|------------------|--------------|
| Pb device | 245°C ±5°C | 5sec±1sec |
| Pb-Free device | 260°C +0/-5°C | 5sec±1sec |



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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